

App. No. 10/761,081  
Office Action Dated May 4, 2005

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listing of claims in the application.

Claim 9 is amended.

**Listing of Claims:**

1-8 (Canceled)

9. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming an electrode pad to come in contact with a surface of a semiconductor substrate provided with a desirable element region or a wiring layer provided on the surface of the semiconductor substrate;

forming an intermediate layer on a surface of the electrode pad;

forming a pad layer to be a bonding pad on a surface of the intermediate layer and patterning the intermediate layer and the pad layer after forming the pad layer; and

forming a resin insulating film to cover edges of patterns of the bonding pad and the intermediate layer.

10. (Original) The method of manufacturing a semiconductor device according to claim 9, wherein the step of forming a resin insulating film includes a step of applying a polyimide resin film.

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11. (Previously Presented) The method of manufacturing a semiconductor device according to claim 9, wherein the step of forming an intermediate layer includes a step of forming a titanium tungsten (TiW) layer by a sputtering method.

12. (Original) The method of manufacturing a semiconductor device according to claim 11, wherein the step of forming a pad layer includes a step of forming a metal layer by sputtering.